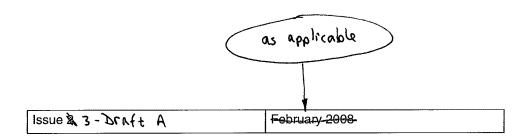


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TRANSISTORS, HIGH VOLTAGE, NPN

BASED ON TYPE 2N3439 AND 2N3440

ESCC Detail Specification No. 5203/011







as applicable

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DOCUMENTATION CHANGE NOTICE

(Refer to https://escies.org for ESCC DCR content)

DCR No.	CHANGE DESCRIPTION
SEE CEBA	Specification up issued to incorporate editorial and technical changes per DCRs.

447, tha

1.5 **MAXIMUM RATINGS**

The maximum ratings shall not be exceeded at any time during use or storage. Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Collector-Base Voltage Variants 01 to 04 Variants 05 to 08	V _{CBO}	450 300	V	Over T _{op}
Collector-Emitter Voltage Variants 01 to 04 Variants 05 to 08	V _{CEO}	350 250	V	Over T _{op}
Emitter-Base Voltage	V _{EBO}	7	V	Over T _{op}
Collector Current	I _C	1	Α	
Power Dissipation	P _{tot1}	800	mW	At T _{amb} ≤ +25°C
	P _{tot2}	5	W	At T _{case} ≤ +25°O
Operating Temperature Range	T _{op}	-65 to +200	°C	Note 🧸 🚺
Storage Temperature Range	T _{stg}	-65 to +200	°C	Note 🎗 🚹
Soldering Temperature	T _{sol}	+260	°C	Note 🧣 2

NOTES:

For T_{amb} or T_{case} > +25°C, derate linearly to 0W at +200°C.
For Variants with tin-lead plating or hot solder dip lead finish all testing performed at T_{amb} > +125°C shall be carried out in a 100% inert atmosphere.

Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

Thermal Resistance, Junction-to-Ambient	Ruh(j-a)	218.8	°c/W	
Thermal Resistance, Junction - to - Case	Rth(j-c)	35	°C/W	



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2.7 POWER BURN-IN CONDITIONS

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T _{amb}	+25 🕸 (+0-5)	°C
Power Dissipation	P _{tot}	800	mW
Collector-Emitter Voltage Variants 01, 02, 03, 04 Variants 05, 06, 07, 08	V _{CE}	250 180	V

NOTES:

2.8 OPERATING LIFE CONDITIONS

The conditions shall be as specified for Power Burn-in.

^{1.} No heat sink nor forced air directly on the device shall be permitted.



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APPENDIX 'A'

AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS		
Deviations from Room Temperature Electrical Measurements	All AC characteristics (Room Temperature Electrical Measurement Note 3) may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes AC characteristic measurements per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.		
Deviations from High and Low Temperatures Electrical Measurements	All characteristics specified may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes characteristic measurements at high and low temperatures per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.		
Deviations from Screening Tests - Chart F3	Solderability is not applicable unless specifically stipulated in the Purchase Order.		

(Approved DCR 447 refers)